ABSTRACT OF THE DISCLOSURE

What is described here is a process for the initial growth of nitrogenous semiconductor crystal materials in the form $A_xB_yC_zN_vM_w$ wherein A, B, C is an element of group II or III, N is nitrogen, M represents an element of group V or VI, and X, Y, Z, W denote the molar fraction of each element of this compound, using a, which are deposited on sapphire, SiC or Si, using various ramp functions permitting a continuous variation of the growth parameters during the initial growth.

~~This novel initial growth process is characterised by the aspect that during the initial~~ growth process ~~of the~~ nitrogenous semiconductor crystal materials on sapphire, SiC or Si an abrupt change of ~~the growth~~ regime is not required for realising a ~~structure suitable for the ongoing high-temperature growth~~.